White LED in 3 mm T 1 Waterclear Package



DESCRIPTION

SHA

High Intensity LED with typical color coordinates x = 0.33, y = 0.33 (typical color temperature 5500 k). This LED emits white light with a high color rendering index.

The emission spectrum is tuned for ideal white, without the impression of being blue shaded or "cold". The package is a standard 3 mm.

The internal reflector is filled with a compound of TAG phosphor and an elastic resin.

Therefore the chip is better protected against temperature cycle stress.

The phosphor converts the blue emission of the InGaN chip partially to amber, which mixes with the remaining blue to produce white.

FEATURES

- High efficient InGaN technology
- Chromaticity coordinate categorized according to CIE1931 per packing unit
- Typical chromaticity coordinates x = 0.33; v = 0.33
- Typical color temperature 5500 K
- ESD-withstand voltage up to 1 kV acc. to JESD22-A114-B
- · Small viewing angle, high luminous intensity
- Chip embedded in elastic resin, improved robustness against temperature cycle stress
- Lead (Pb)-free device
- · RoHS compliant

APPLICATIONS

- Indicator and backlighting
- Indoor and outdoor message panels
- · Alternative to incandescent lamps
- · Marker lights

PRODUCT GROUP AND PACKAGE DATA

- Product group: LED
- Package: 3 mm
- · Product series: standard
- Angle of half intensity: ± 16°

PARTS TABLE				
PART	COLOR, LUMINOUS INTENSITY	TECHNOLOGY		
VLHW4900	White, $I_V > 240 \text{ mcd}$	InGaN/TAG on SiC		
VLHW4902	White, $I_V = (430 \text{ to } 2000) \text{ mcd}$	InGaN/TAG on SiC		





ABSOLUTE MAXIMUM RATINGS ¹⁾ VLHW490.				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage ²⁾		V _R	5	V
DC Forward current	$T_{amb} \le 50 \ ^{\circ}C$	١ _F	30	mA
Surge forward current	t _p ≤ 10 μs	I _{FSM}	0.1	А
Power dissipation		P _V	126	mW
Junction temperature		Tj	100	°C
Operating temperature range		T _{amb}	- 40 to + 100	°C
Storage temperature range		T _{stg}	- 40 to + 100	°C
Soldering temperature	$t \le 5 s$	T _{sd}	260	°C
Thermal resistance junction/ ambient		R _{thJA}	400	K/W

Note:

 $^{1)}$ T_{amb} = 25 °C, unless otherwise specified $^{2)}$ Driving the LED in reverse direction is suitable for short term application

OPTICAL AND ELECTRICAL CHARACTERISTICS ¹⁾ WHITE VLHW490.							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN	TYP.	MAX	UNIT
Luminous intensity ²⁾	I _F = 20 mA	VLHW4900	Ι _V	240	500		mcd
		VLHW4902	Ι _V	430		2000	mcd
Luminous flux	I _F = 20 mA		φv		250		mlm
Chromaticity coordinate x acc. to CIE 1931	I _F = 20 mA		x		0.33		
Chromaticity coordinate y acc. to CIE 1931	I _F = 20 mA		у		0.33		
Angle of half intensity	I _F = 20 mA		φ		± 16		deg
Forward voltage	I _F = 20 mA		V _F		3.5	4.2	V
Reverse voltage	I _R = 10 μA		V _R	5			V
Temperature coefficient of V_F	I _F = 20 mA		TCV		- 4		mV/K
Temperature coefficient of ${\rm I}_{\rm V}$	I _F = 20 mA		TCI		- 0.5		% / K

Note: ¹⁾ $T_{amb} = 25 \text{ °C}$, unless otherwise specified ²⁾ in one Packing Unit I_{Vmin}/I_{Vmax} ≤ 0.5

CHROMATICITY COORDINATE CLASSIFICATION				
GROUP)	X		
	MIN	MAX	MIN	МАХ
3	0.280	0.325	0.210	0.340
4	0.305	0.350	0.260	0.390
5	0.330	0.375	0.310	0.440

LUMINOUS INTENSITY CLASSIFICATION				
GROUP	LIGHT INTENSITY (MCD)			
STANDARD	MIN MAX			
Z	240	480		
AA	320	640		
BB	430	860		
CC	575	1150		
DD	750	1500		
EE	1000	2000		



VLHW490. Vishay Semiconductors

TYPICAL CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

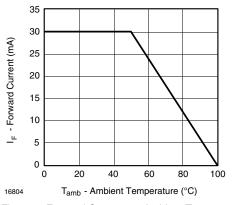


Figure 1. Forward Current vs. Ambient Temperature

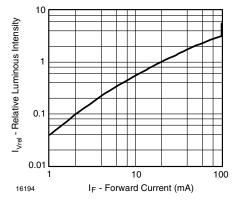


Figure 2. Relative Luminous Intensity vs. Forward Current

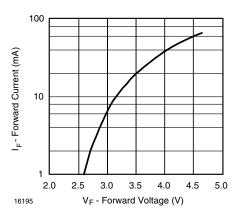
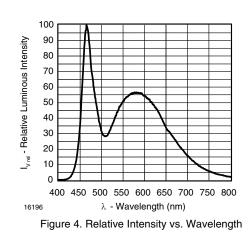


Figure 3. Forward Current vs. Forward Voltage



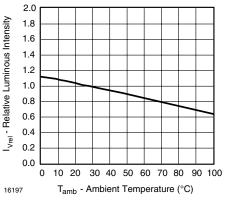


Figure 5. Rel. Luminous Intensity vs. Ambient Temperature

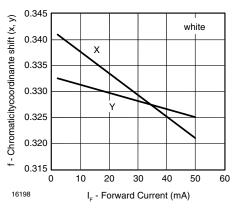


Figure 6. Chromaticity Coordinate Shift vs. Forward Current

VLHW490.

Vishay Semiconductors



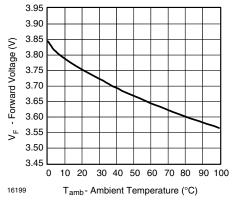


Figure 7. Forward Voltage vs. Ambient Temperature

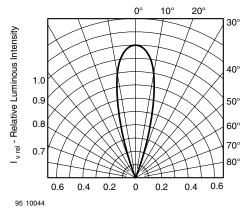
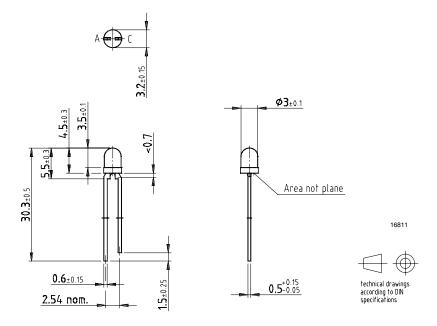
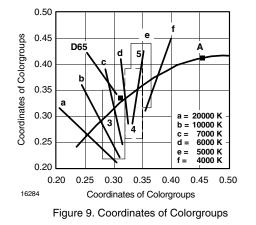


Figure 8. Rel. Luminous Intensity vs. Angular Displacement

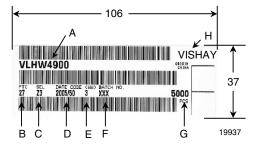
PACKAGE DIMENSIONS in millimeters







BAR CODE PRODUCT LABEL



- A) Type of component
- B) Manufacturing plant
- C) SEL selection code (bin):
 - e.g.: Z = code for luminous intensity group 3 = code for chromaticity coordinate
- D) Date code year/week
- E) Day code (e.g. 1: Monday)
- F) Batch no.
- G) Total quantity
- H) Company code



Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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